

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|-------|---|----------------------------|------------------|---------|------------------|
| L1 | 0 | ("(gatewith(controlfloating)) withmemory").PN | US-PGPU B; USPAT; EPO; JPO | OR | OFF | 2004/12/01 13:35 |
| L2 | 0 | (gate with (controlfloating)) with memory | US-PGPU B; USPAT; EPO; JPO | OR | ON | 2004/12/01 13:36 |
| L3 | 30062 | (gate with (control floating)) with memory | US-PGPU B; USPAT; EPO; JPO | OR | ON | 2004/12/01 13:36 |
| L4 | 22375 | 3 and (source drain) | US-PGPU B; USPAT; EPO; JPO | OR | ON | 2004/12/01 13:38 |
| L5 | 13304 | 4 and (stack\$3 wordline word adj line) | US-PGPU B; USPAT; EPO; JPO | OR | ON | 2004/12/01 13:37 |
| L6 | 3904 | 5 and ((source drain) with (contact\$3 stud plug pillar)) | US-PGPU B; USPAT; EPO; JPO | OR | ON | 2004/12/01 13:39 |
| L7 | 3927 | 5 and ((source drain) with (contact\$3 stud\$3 plug pillar)) | US-PGPU B; USPAT; EPO; JPO | OR | ON | 2004/12/01 13:39 |
| L8 | 3893 | 7 and (dielectric insulat\$3 conduct\$4 oxide polysilicon) | US-PGPU B; USPAT; EPO; JPO | OR | ON | 2004/12/01 13:42 |
| L9 | 1097 | 8 and ((silicide salicide metal adj refractory) with (gate source drain)) | US-PGPU B; USPAT; EPO; JPO | OR | ON | 2004/12/01 13:47 |
| L10 | 1028 | 9 and (trench hole via hole opening) | US-PGPU B; USPAT; EPO; JPO | OR | ON | 2004/12/01 13:48 |
| L11 | 988 | 10 and (silicide with (source drain plug contact stud gate)) | US-PGPU B; USPAT; EPO; JPO | OR | ON | 2004/12/01 14:03 |
| L12 | 470 | 11 and (silicide with (control adj gate)) | US-PGPU B; USPAT; EPO; JPO | OR | ON | 2004/12/01 14:04 |
| L13 | 170 | 12 and (silicide with (source drain)) | US-PGPU B; USPAT; EPO; JPO | OR | ON | 2004/12/01 14:05 |

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|-----|---|---------------|-----------------|----|----|---------------------|
| L14 | 1 | "6387784".PN. | USPAT; USOCR | OR | ON | 2004/12/01 14:43 |
| L15 | 1 | "6159800".PN. | USPAT; USOCR | OR | ON | 2004/12/01 14:43 |
| L16 | 1 | "6103576".PN. | USPAT; USOCR | OR | ON | 2004/12/01 14:44 |
| L17 | 1 | "5521108".PN. | USPAT; USOCR | OR | ON | 2004/12/01 14:44 |
| L18 | 1 | "4775642".PN. | USPAT; USOCR | OR | ON | 2004/12/01 14:44 |

EAST - [2324.jsp:1]

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Active

- L3: (30062) (gate with (control floating)) with memory
- L4: (22375) 3 and (source drain)
- L5: (13304) 4 and (stack\$3 wordline word adj line)
- L6: (3904) 5 and ((source drain) with (contact\$3 stud plug pillar))
- L7: (3927) 5 and ((source drain) with (contact\$3 stud\$3 plug pillar))
- L8: (3893) 7 and (dielectric insulat\$3 conduct\$4 oxide polysilicon)
- L9: (1097) 8 and ((silicide salicide metal adj refractory) with (gate source drain))
- L10: (1028) 9 and (trench hole via hole opening)
- L11: (988) 10 and (silicide with (source drain plug contact stud gate))
- L12: (470) 11 and (silicide with (control adj gate))
- L13: (170) 3 and (silicide with (source drain))

12 and (silicide with (source drain))

US POPUS PAT EPC JP

Default Expansion: OR

Buttons: Browse, Clear, Search, Highlight all hit terms exactly

Buttons: EPS form, IS&P form, Image, Text, HTML

| | U | I | Document ID | Issue Date | Pages | Title | Current OR | Current XR | Retrieval C | Inventor | S | C | P | | | | | | |
|----|--------------------------|--------------------------|-----------------|------------|-------|--|------------|------------|-------------|----------------------------|--------------------------|--------------------------|--------------------------|--------------------------|--------------------------|--------------------------|--------------------------|--------------------------|--------------------------|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 20041023810A | 20041118 | 34 | Nonvolatile semiconductor memory and read method | 365/222 | | | Sato, Hiroshi et al. | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 20041023780 | 20041111 | 62 | Semiconductor device | 365/202 | | | Shukuri, Shoji et al. | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | US 20041021430A | 20041028 | 50 | Nonvolatile semiconductor memory device and method | 438/257 | | | Shimizu, Shu | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | US 20041020700 | 20041021 | 24 | Two mask floating gate EEPROM and method of making | 257/314 | | | Kouznetsov, Igor G. et al. | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 5 | <input type="checkbox"/> | <input type="checkbox"/> | US 20041019561A | 20040923 | 91 | Semiconductor integrated circuit device and method | 438/257 | | | Shukuri, Shoji | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 6 | <input type="checkbox"/> | <input type="checkbox"/> | US 20041019561A | 20040923 | 47 | Nonvolatile memories and methods of fabrication | 438/257 | 438/258 | | Ding, Yi | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 7 | <input type="checkbox"/> | <input type="checkbox"/> | US 20041017040A | 20040916 | 71 | Data writing method for semiconductor memory device | 365/185.22 | | | Noguchi, Mitsuhiro et al. | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 8 | <input type="checkbox"/> | <input type="checkbox"/> | US 20041015009A | 20040819 | 40 | Method of manufacturing a semiconductor integrated circuit | 257/331 | | | Lee, Sang-Eun et al. | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 9 | <input type="checkbox"/> | <input type="checkbox"/> | US 20041015009A | 20040819 | 18 | Non-volatile semiconductor memory device and method | 257/315 | | | Hakozaki, Kenji et al. | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 10 | <input type="checkbox"/> | <input type="checkbox"/> | US 20041014500A | 20040729 | 20 | Non-volatile memory device having dual gates and method | 257/321 | | | Min, Hong-Kook et al. | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 11 | <input type="checkbox"/> | <input type="checkbox"/> | US 20041012510A | 20040715 | 16 | Cell structure of non-volatile memory device and method | 257/315 | | | Lee, Tae-Jung et al. | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 12 | <input type="checkbox"/> | <input type="checkbox"/> | US 20041011010A | 20040624 | 11 | Non-volatile memory device having improved programming | 257/315 | | | Kang, Sung-Taeg | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 13 | <input type="checkbox"/> | <input type="checkbox"/> | US 20040527 | 20040527 | 19 | FOUR-BIT NON-VOLATILE | 365/185.03 | | | Rojzin, Yakov et al. | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |

